

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSIII)

2SK2607

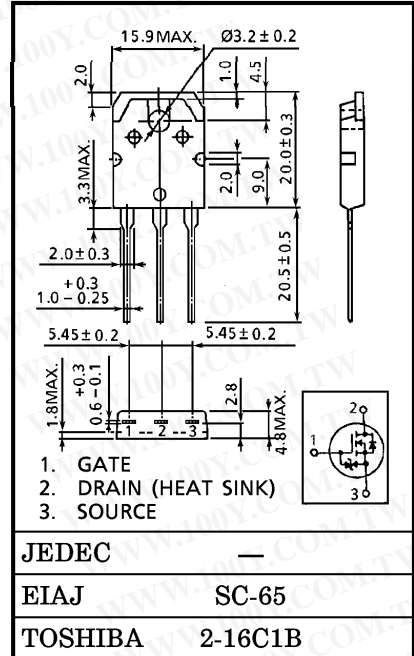
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

INDUSTRIAL APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 1.0\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 7.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 640V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V, I_D = 1mA$)



Weight : 4.6g

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	800	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	800	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	I_D	9
	Pulse	I_{DP}	27
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	150	W
Single Pulse Avalanche Energy**	E_{AS}	778	mJ
Avalanche Current	I_{AS}	9	A
Repetitive Avalanche Energy*	E_{AR}	15	mJ
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

Note ;

- * Repetitive rating ; Pulse Width Limited by Max. junction temperature.
- ** $V_{DD} = 90V$, Starting $T_{ch} = 25^\circ C$, $L = 17.4mH$
 $R_G = 25\Omega$, $I_{AR} = 9A$

**This transistor is an electrostatic sensitive device.
 Please handle with caution.**

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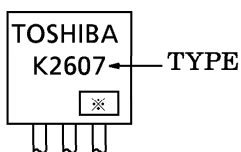
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±30V, VDS = 0V	—	—	±10	μA
Gate-Source Breakdown Voltage		V(BR)GSS	IG = ±10μA, VDS = 0V	±30	—	—	V
Drain Cut-off Current		IDSS	VDS = 640V, VGS = 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V(BR)DSS	ID = 10mA, VGS = 0V	800	—	—	V
Gate Threshold Voltage		Vth	VDS = 10V, ID = 1mA	2.0	—	4.0	V
Drain-Source ON Resistance		RDS(ON)	VGS = 10V, ID = 4A	—	1.0	1.2	Ω
Forward Transfer Admittance		Yfs	VDS = 15V, ID = 4A	3.0	7.0	—	S
Input Capacitance		Ciss	VDS = 25V, VGS = 0V, f = 1MHz	—	2160	—	pF
Reverse Transfer Capacitance		Crss		—	45	—	
Output Capacitance		Coss		—	200	—	
Switching Time	Rise Time	tr	<p> V_{GS} 10V 0V $I_D = 4A$ $R_L = 100\Omega$ $V_{DD} \doteq 400V$ </p>	—	25	—	ns
	Turn-on Time	ton		—	60	—	
	Fall Time	tf		—	25	—	
	Turn-off Time	t _{off}		—	110	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 400V, VGS = 10V, ID = 9A	—	68	—	nC
Gate-Source Charge		Qgs		—	38	—	
Gate-Drain ("Miller") Charge		Qgd		—	30	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	9	A
Pulse Drain Reverse Current	IDRP	—	—	—	27	A
Diode Forward Voltage	VDSF	IDR = 9A, VGS = 0V	—	—	-1.9	V
Reverse Recovery Time	t _{rr}	IDR = 9A, VGS = 0V	—	1000	—	ns
Reverse Recovery Charge	Q _{rr}	dIDR / dt = 100A / μs	—	12	—	μC

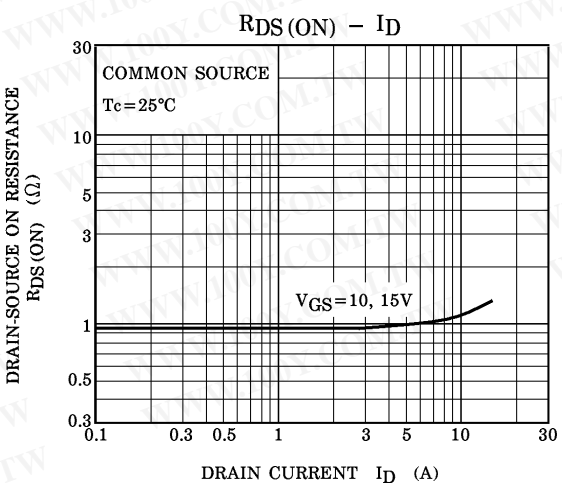
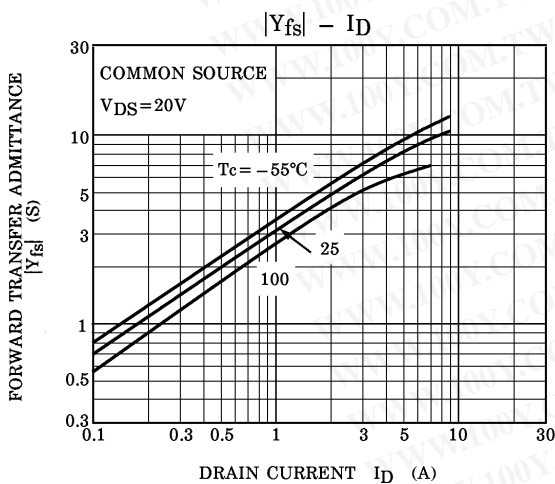
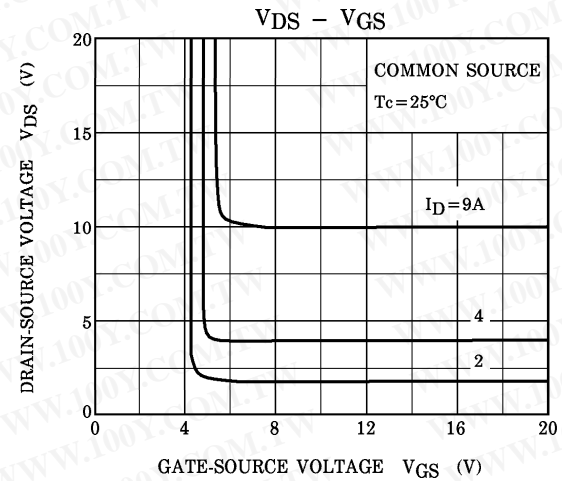
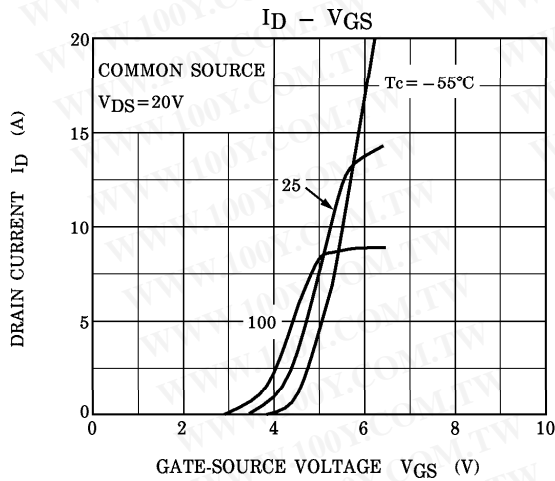
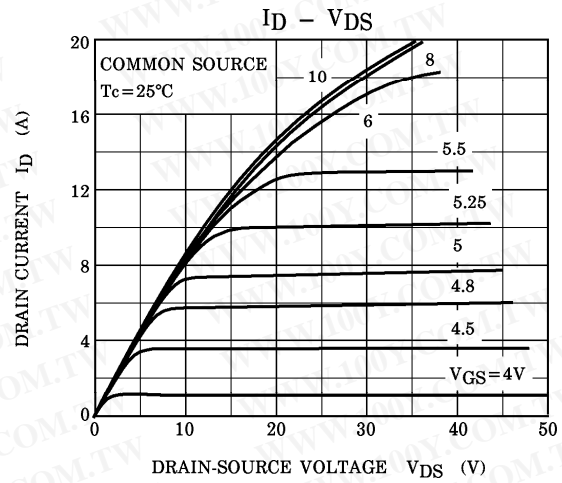
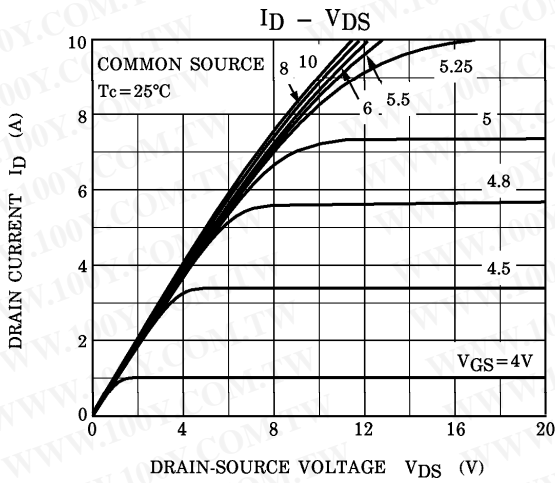
MARKING

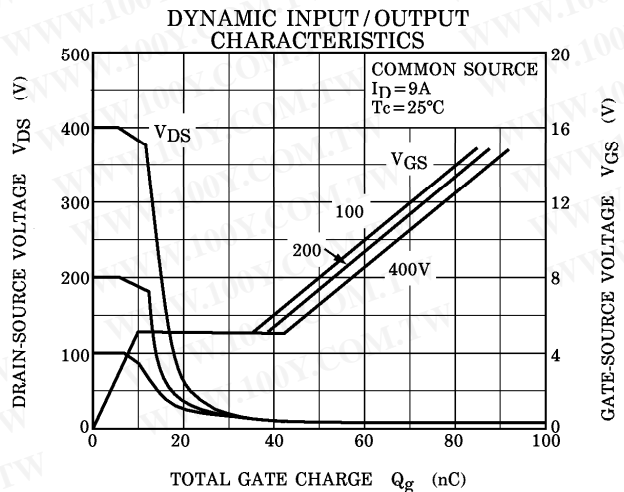
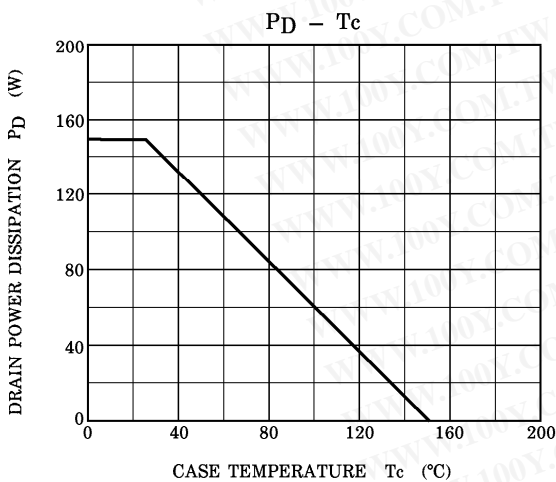
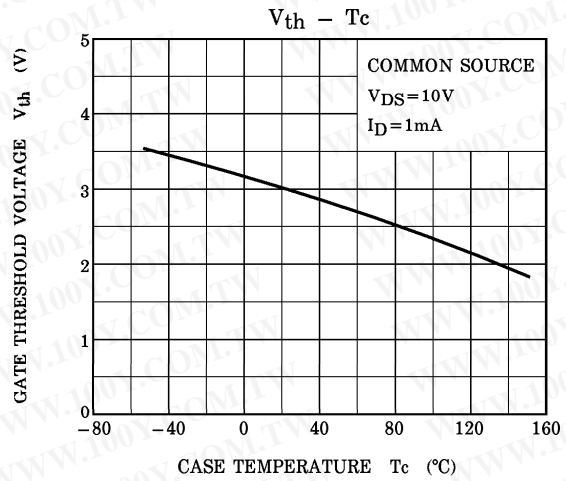
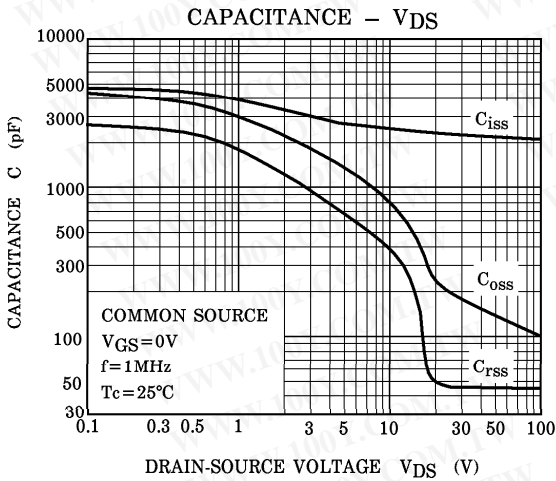
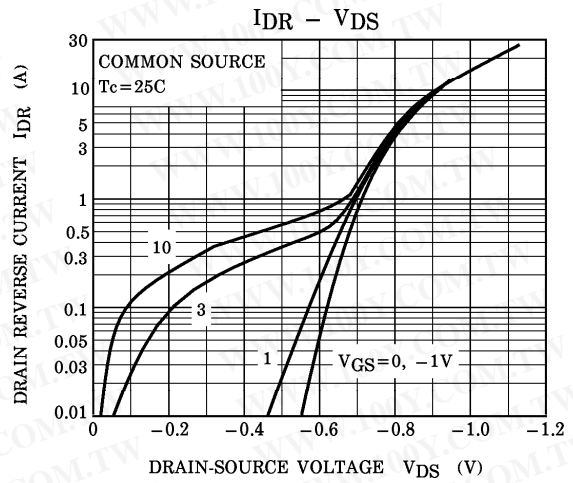
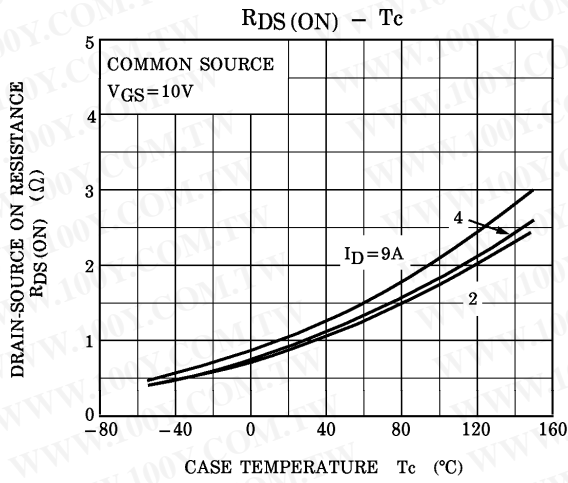


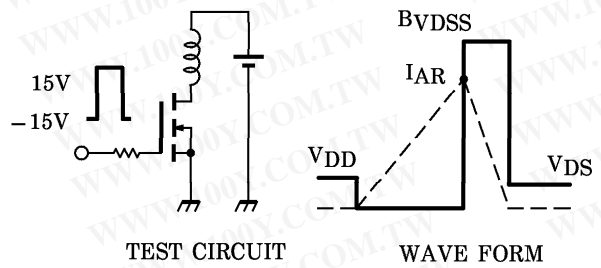
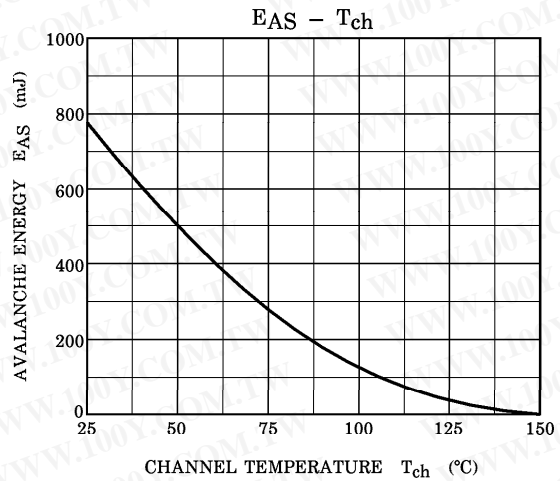
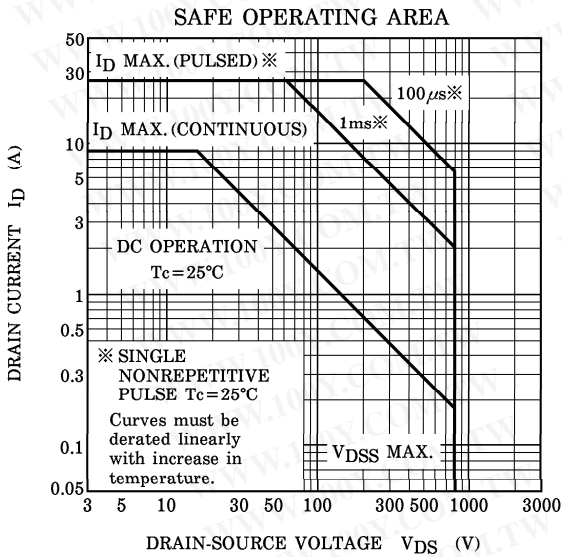
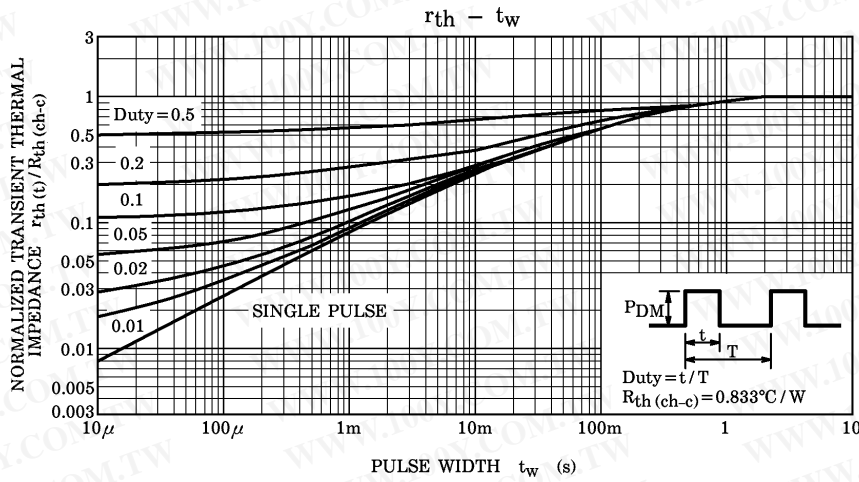
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 9A$, $R_G = 25\Omega$
 $V_{DD} = 90V$, $L = 17.4mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$